L Number	Hits	Search Text	Lop	Time et emp
1	26	5676587.pn. 5853604.uref. 5827781.uref.	DB USPAT;	Time stamp 2003/03/06 11:00
-	20	00.000.pm. 000004.dref. 002//01.dref.	US-PGPUB	2003/03/00 11:00
2	2	5853604.pn. 5827781.pn.	USPAT;	2003/03/06 11:20
-	_		US-PGPUB	2003/03/00 11:20
3	5	("4193226" "4811522" "4963283"	USPAT	2003/03/06 11:02
		"5391258" "5421769").PN.		2000,00,00 11102
4	5	("3691694" "5081421" "5536202"	USPAT	2003/03/06 11:03
		"5643405" "5733177").PN.		
5	8	5733177.uref.	USPAT;	2003/03/06 11:40
			US-PGPUB	+
6	5101	438/626.ccls. 438/633.ccls. 438/687.ccls.	USPAT;	2003/03/06 11:42
		438/690.ccls. 438/691.ccls. 438/692.ccls.	US-PGPUB	
i _		451/41.ccls.		
7	210	(438/626.ccls. 438/633.ccls.	USPAT;	2003/03/06 11:43
		438/687.ccls.) and (438/690.ccls.	US-PGPUB	j
! ! 8	389	438/691.ccls. 438/692.ccls. 451/41.ccls.)		0000/00/06 11 40
0	369	(438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls. 438/691.ccls. 438/692.ccls.	USPAT;	2003/03/06 11:49
[450/090.ccis. 450/091.ccis. 450/092.ccis. 451/41.ccls.) and (relative near2 (speed	US-PGPUB	
		velocity))		İ
10	2041	((cmp (chemical near mechanical)) with	EPO; JPO;	2003/03/06 11:50
1	2041	(copper cu conduct\$4 metal))	DERWENT;	2003/03/00 11.30
		(copper ou conduce; metaly)	IBM TDB	
12	8908	((cmp (chemical near mechanical)) with	USPAT;	2003/03/06 11:51
		(copper cu conduct\$4 metal))	US-PGPUB	
13	8	(((cmp (chemical near mechanical)) with	USPAT;	2003/03/06 14:14
		(copper cu conduct\$4 metal))) same	US-PGPUB	
		(relative near2 (speed velocity))		İ
9	93	((438/626.ccls. 438/633.ccls.	USPAT;	2003/03/06 12:04
		438/687.ccls. 438/690.ccls. 438/691.ccls.	US-PGPUB	
		438/692.ccls. 451/41.ccls.) and (relative		
		near2 (speed velocity))) and ((cmp		
		(chemical near mechanical)) with (copper		
		cu conduct\$4 metal))		2002/02/06 14 12
14	2	((438/626.ccls. 438/633.ccls.	USPAT;	2003/03/06 14:13
		438/687.ccls.) and (438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.))	US-PGPUB	
		and (relative near2 (speed velocity))		
15	14	(((cmp (chemical near mechanical)) with	USPAT;	2003/03/06 14:21
	+7	(copper cu conduct\$4 metal))) same	US-PGPUB	2003/03/00 11.21
		((relative linear) near2 (speed velocity))		
16	16	(((cmp (chemical near mechanical)) with	USPAT;	12003/03/06 14:23 ;
	İ	(copper cu conduct\$4 metal))) same	US-PGPUB	
		((rotat\$6 near2 (speed velocity)) rpm		
[rpms) same (change decreas\$4 reduc\$5)	1	
11	3	(((cmp (chemical near mechanical)) with	EPO; JPO;	2003/03/06 14:38
		(copper cu conduct\$4 metal))) and	DERWENT;	
		(relative near2 (speed velocity))	IBM_TDB	2002/02/05 25 22
17	1888	(cmp (chemical near mechanical) polish\$4)	USPAT;	2003/03/06 15:02
		<pre>and ((carrier head) same (retain\$4 ring membrane)) and (wafer substrate) and</pre>	US-PGPUB	
		membrane)) and (water substrate) and (platen pad)		
18	505	(praten pad) (cmp (chemical near mechanical) polish\$4)	USPAT;	2003/03/06 15:03
1 10	303	and ((carrier head) same (retain\$4 ring	US-PGPUB	2303,03,00 13.03
		membrane) same (platen pad) same (pressure		
	ļ	psi pa)) and (wafer substrate)		
19	501	(438/626.ccls. 438/633.ccls. 438/687.ccls.	USPAT;	2003/03/06 14:49
-		438/690.ccls. 438/691.ccls. 438/692.ccls.	US-PGPUB	
ĺ		451/41.ccls.) and ((cmp (chemical near		
		mechanical) polish\$4) and ((carrier head)		
		same (retain\$4 ring membrane)) and (wafer		
		substrate) and (platen pad))		1 0000 100 100 111 151
20	203		USPAT;	2003/03/06 14:49
, ,	,	438/690.ccls. 438/691.ccls. 438/692.ccls.	US-PGPUB	
ŧ	1	451/41.ccls.) and ((cmp (chemical near		
!		<pre>mechanical) polish\$4) and ((carrier head) same (retain\$4 ring membrane) same (platen</pre>		
		pad) same (pressure psi pa)) and (wafer		
ļ		substrate))		
<u> </u>		Substitute, i	<u> </u>	

22	787	((cmp (chemical near mechanical) polish\$4)	USPAT;	2003/03/06 14:54
		with (copper cu conduct\$4 metal)) and	US-PGPUB	
		((carrier head) same (retain\$4 ring		
		membrane)) and (wafer substrate) and		
		(platen pad)		
23	231		USPAT;	2003/03/06 14:57
		with (copper cu conduct\$4 metal)) and	US-PGPUB	
		((carrier head) same (retain\$4 ring		į
!	1	membrane) same (platen pad) same (pressure	1	,
25	249	psi pa)) and (wafer substrate) (cmp (chemical near mechanical) polish\$4)	EPO; JPO;	2003/03/06 15:02
23	249	and ((carrier head) same (retain\$4 ring	DERWENT;	2003/03/06 15:02
		membrane)) and (platen pad)	IBM TDB	
21	83	(cmp (chemical near mechanical) polish\$4)	USPAT;	2003/03/06 15:04
		and ((carrier head) same (retain\$4 ring)	US-PGPUB	2003,03,00 13.01
		same membrane same (platen pad) same	00 10102	
		(pressure psi pa)) and (wafer substrate)		
24	112	(438/626.ccls. 438/633.ccls. 438/687.ccls.	USPAT;	2003/03/06 16:00
		438/690.ccls. 438/691.ccls. 438/692.ccls.	US-PGPUB	
		451/41.ccls.) and (((cmp (chemical near		
		mechanical) polish\$4) with (copper cu		
		conduct\$4 metal)) and ((carrier head) same		
		(retain\$4 ring membrane) same (platen pad)		
		same (pressure psi pa)) and (wafer		
27	111	substrate))	EDO. TDO.	2002/02/06 17:01
21	111	(tamp	EPO; JPO;	2003/03/06 17:01
		and ((carrier head) same (retain\$4 ring membrane)) and (platen pad)) and (pressure	DERWENT; IBM TDB	
		psi pa copper cu metal conduct\$4)	1511-100	
_	1	6204181.pn.	USPAT;	2003/03/06 09:48
	_		US-PGPUB	2000,00,00
-	1	20010004538.pn.	USPAT;	2003/03/05 17:55
ĺ	į	•	US-PGPUB	